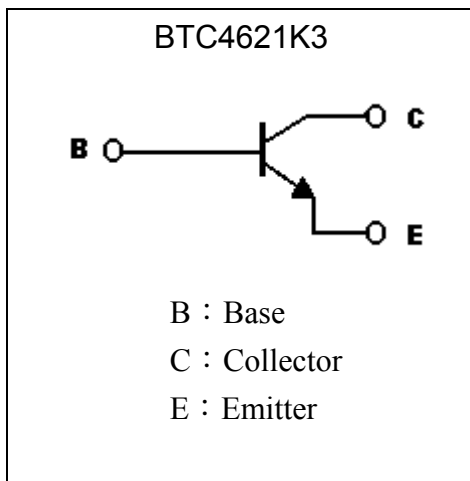


**High Voltage NPN Epitaxial Planar Transistor**

# BTC4621K3

**Features**

- High breakdown voltage. ( $BV_{CEO}=350V$ )
- Low saturation voltage, typically  $V_{CE(sat)}=0.1V$  at  $I_C/I_B=10mA/1mA$ .
- Pb-free package

**Symbol**

**Absolute Maximum Ratings** ( $T_a=25^{\circ}C$ )

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	$V_{CBO}$	350	V
Collector-Emitter Voltage	$V_{CEO}$	350	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current (DC)	$I_C$	100	mA
Collector Current (Pulse)	$I_{CP}$	200	
Base Current	$I_B$	50	mA
Power Dissipation ( $T_A=25^{\circ}C$ )	$P_D$	1	W
Junction Temperature	$T_j$	150	$^{\circ}C$
Storage Temperature	$T_{stg}$	-55~+150	$^{\circ}C$



**Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CB0</sub>	350	-	-	V	I <sub>C</sub> =50μA, I <sub>E</sub> =0
BV <sub>CEO</sub>	350	-	-	V	I <sub>C</sub> =1mA, I <sub>B</sub> =0
BV <sub>EBO</sub>	6	-	-	V	I <sub>E</sub> =50μA, I <sub>C</sub> =0
I <sub>CB0</sub>	-	-	0.1	μA	V <sub>CB</sub> =300V, I <sub>E</sub> =0
I <sub>EBO</sub>	-	-	0.1	μA	V <sub>EB</sub> =6V, I <sub>C</sub> =0
*V <sub>CE(sat)</sub>	-	0.1	0.6	V	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA
*V <sub>BE(sat)</sub>	-		1	V	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA
h <sub>FE</sub>	100	-	320	-	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA
f <sub>T</sub>	-	70	-	MHz	V <sub>CE</sub> =30V, I <sub>C</sub> =10mA, f=10MHz
Cob	-	2.6	-	pF	V <sub>CB</sub> =30V, f=1MHz

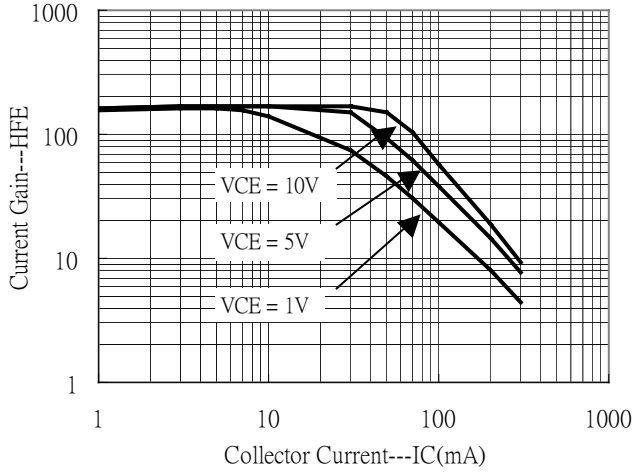
\*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

**Classification Of hFE**

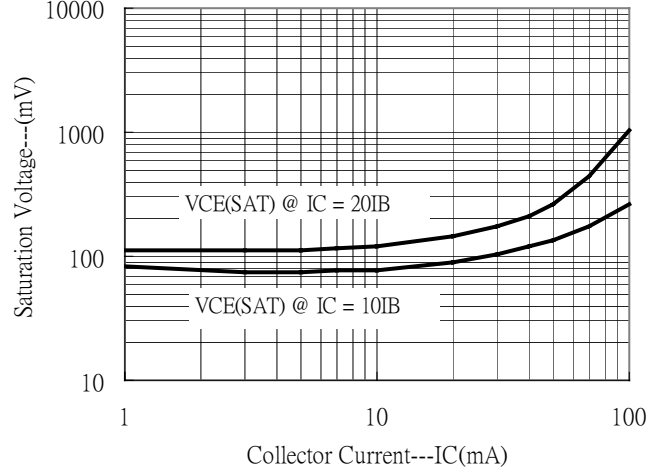
Rank	E	F
Range	100~200	160~320

**Characteristic Curves**

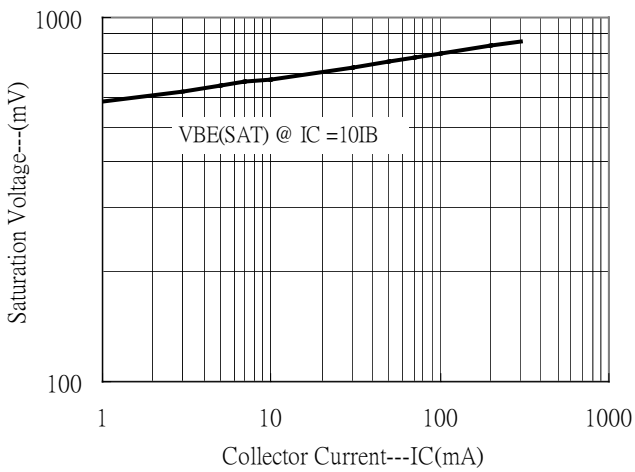
Current Gain vs Collector Current



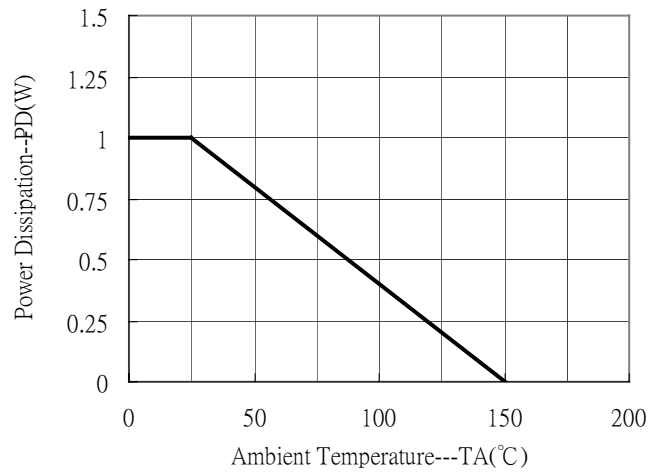
Saturation Voltage vs Collector Current



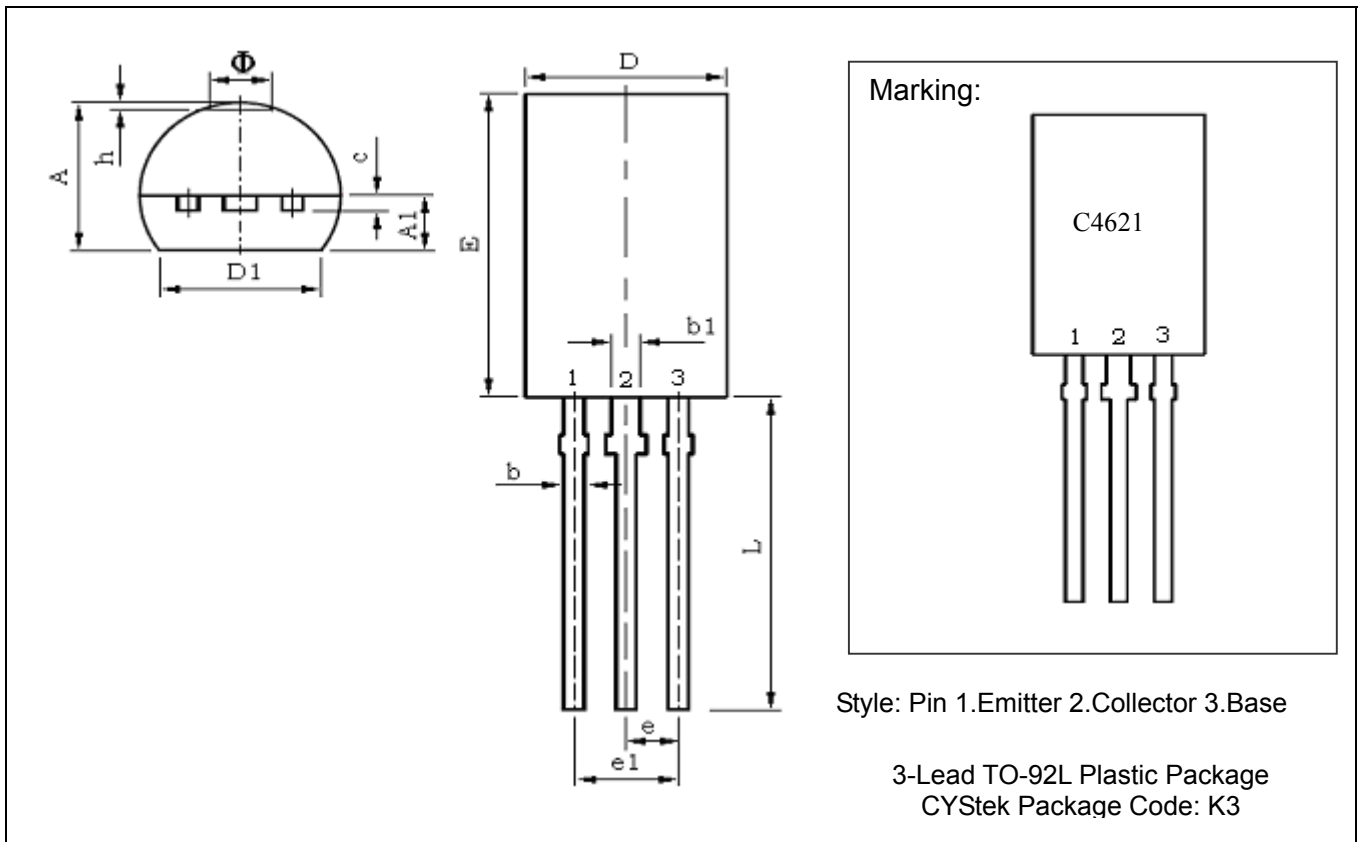
Saturation Voltage vs Collector Current



Power Derating Curve



**TO-92L Dimension**



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.146	0.161	3.700	4.100	E	0.307	0.323	7.800	8.200
A1	0.050	0.062	1.280	1.580	e	*0.050		*1.270	
b	0.014	0.022	0.350	0.550	e1	0.096	0.104	2.440	2.640
b1	0.024	0.031	0.600	0.800	L	0.543	0.559	13.800	14.200
c	0.014	0.018	0.350	0.450	Φ	-	0.063	-	1.600
D	0.185	0.201	4.700	5.100	h	0.000	0.012	0.000	0.300
D1	0.157	-	4.000	-					

Notes: 1. Controlling dimension: millimeters.  
 2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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